

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	331.00 +/- 5.00 $\mu$ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 $\mu$ m	Guaranteed by Process
	7.0	Bow	<60.00 $\mu$ m	ADE to ASTM F534, 20%
	8.0	Warp	<60.00 $\mu$ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	325.00 +/- 5.00 $\mu$ m	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	1 -10 Ohm cm	Wafer Vendor
	17.0	Backside Finish	Polished with 200nm +/- 5% oxide and lasermark	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
DeviceSilicon	20.0	Device Growth Method	CZ	Wafer Vendor
	21.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	22.0	Nominal Thickness	5.00 +/- 0.50 $\mu$ m	FTIR, 100% 9-Pt (note3)
	23.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	24.0	Device Doping Type	N	Wafer Vendor
	25.0	Device Dopant	Phosphorous	Wafer Vendor
	26.0	Device Resistivity	1 -10 Ohm-cm	Wafer Vendor
	27.0	Buried Layer Implant	none	implant vendor
	28.0	Voids	0	Bright Light, 100% (note 2)
	29.0	Scratches	0	Bright Light, 100% (note 2)
	30.0	Haze	none	Bright Light, 100% (note 2)
31.0	Device Field Oxidation	2,000.00 +/- 100.00 A		

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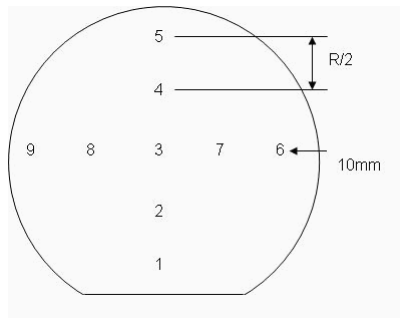
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information